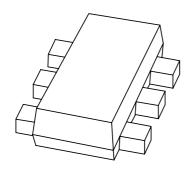
DISCRETE SEMICONDUCTORS

DATA SHEET



PEMT1 PNP general purpose double transistor

Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



NXP Semiconductors Product data sheet

PNP general purpose double transistor

PEMT1

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

· General purpose switching and amplification.

DESCRIPTION

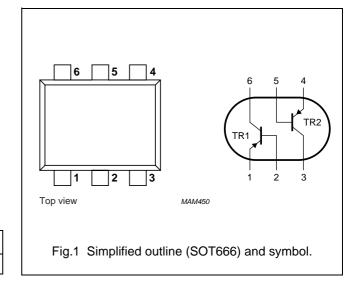
PNP transistor pair in a SOT666 plastic package. NPN complement: PEMX1.

MARKING

TYPE NUMBER	MARKING CODE		
PEMT1	FF		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transis	Per transistor						
V _{CBO}	collector-base voltage	open emitter	_	-50	V		
V _{CEO}	collector-emitter voltage	open base	_	-40	V		
V _{EBO}	emitter-base voltage	open collector	_	-5	V		
I _C	collector current (DC)		_	-100	mA		
I _{CM}	peak collector current		_	-200	mA		
I _{BM}	peak base current		_	-200	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb}	operating ambient temperature		-65	+150	°C		
Per device							
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW		

Note

1. Transistor mounted on an FR4 printed-circuit board.

NXP Semiconductors Product data sheet

PNP general purpose double transistor

PEMT1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering is reflow soldering.

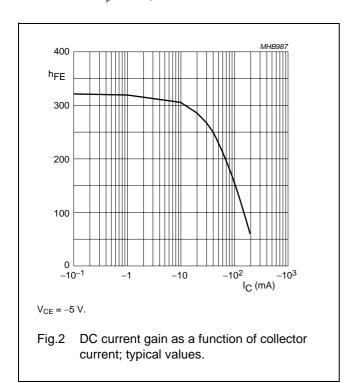
CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor				
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-100	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0$	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -6 \text{ V}; I_{C} = -1 \text{ mA}$	120	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1	_	-200	mV
C _c	collector capacitance	$V_{CB} = -12 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	2.2	pF
f _T	transition frequency	$V_{CE} = -12 \text{ V}; I_{C} = -2 \text{ mA};$ f = 100 MHz	100	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



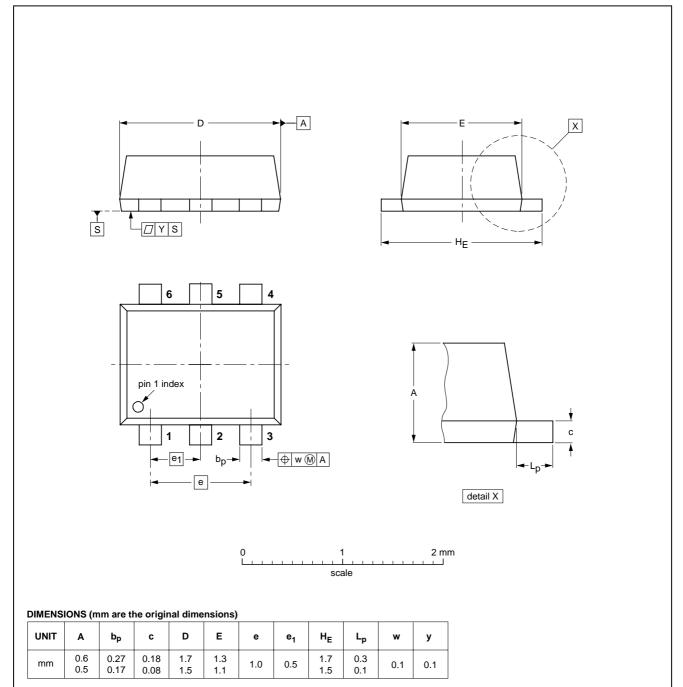
PNP general purpose double transistor

PEMT1

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT666						-01-01-04 01-08-27

NXP Semiconductors Product data sheet

PNP general purpose double transistor

PEMT1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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